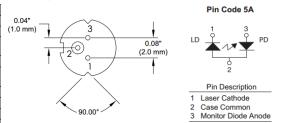


VCSEL Parameters	Test Condition	Symbol	Min.	Тур.	Max.	Units
Optical Power Output	I _F =4mA	Po	0.7	1		mW
Threshold Current		I _{TH}			1.5	mA
Threshold Current Temperature Variation	$T_A = 0$ °C to 70 °C	ΔI_{TH}	-1.5		1.5	mA
Slope Efficiency		η	0.25	0.35	0.6	mW/mA
Slope Efficiency Temperature variation	$T_A = 0$ °C to 70 °C	Δη /ΔΤ		-6000		PPM/°C
Peak Wavelength	I _F =4 mA	λ_{P}	835		870	nm
λ _P Temperature Variation	I _F =4 mA	$\Delta \lambda_{P} \Delta T$		0.06		nm/°C
Laser Forward Voltage	I _F =4 mA	V _F		1.9	2.5	V
Laser Reverse Voltage	$I_R=10 \mu A$	BVR _{LD}		-10		V
Rise and Fall Times	Prebias Above Threshold, 20%-80%	t _r , t _f		150		ps
Series Resistance	I _F =4 mA	R _S	75	110	150	Ohms
Series Resistance Temperature Coefficient	I _F =4 mA, 0°C to 70°C	dR₄/dT		-2000		PPM/°C
Side Mode Suppression Ratio	I _F =4mA	SMSR	15	30		dB
Change in wavelength with current		$\Delta \lambda_{Pl} \Delta I$		0.25		mA/nm
Beam Divergence		Θ_{FWHM}		11	20	Degrees
Photodiode Parameters	Test Condition	Symbol	Min.	Typ.	Max.	Units
Monitor Current	Po = 1mW	I_{PD}		0.035		mA
Monitor current Temperature Variation	Po = 1mW	$\Delta I_{PD}/\Delta T$		0.2		%/°C
Dark Current	Po =0mW, V_R =3V	I_D			20	nA
PD Reverse Voltage	Po =0mW, I _R =10 μA	BVR _{PD}	30	115		V
PD Capacitance	V _R =0V, Freq=1MHz V _R =3V, Freq=1MHz	С		75 40	100 55	pF



Specification	Symbol	Min	Typ	Max
Wavelength, nm	λ _p	640	650	660
Output Power, mW	Po	-	7	10
Threshold Current, mA	I _{th}	-	20	25
Operation Current, mA	Ioo	-	28	35
Operating Voltage, V	V _{op}	-	2.2	2.6
D Di 1	θ _{II}	5	9	12
Beam Divergence, deg	θ_{\perp}	24	28	32
Slope Efficiency, mW/mA	η	0.6	1	1.3
Monitor Current, mA	Im	-	0.12	0.3
Astigmatism, µm	As	-	-	15
Beam Angle Deviation, deg	θ _{//}	-3	-	3
	θ_{\perp}	-3	-	3
Emission Point Accuracy, µm	ΔX	-80		80
	ΔY	-80		80
	ΔZ	-80		80